



Substitute for form 1449A/PTO

**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**

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of

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Application Number	10/695,724
Filing Date	October 28, 2003
First Named Inventor	Eric Frayssinet
Art Unit	2823
Examiner Name	Rori Burch
Attorney Docket Number	15675P314CX

**NON PATENT LITERATURE DOCUMENTS**

Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
Lee		"Selective area epitaxy of GaN for electron field emission devices", D. Kapolnek, et al., Journal of Crystal Growth 170 (1997) pgs 340-343	
		"Selective growth of wurtzite GaN and Al <sub>x</sub> Ga <sub>1-x</sub> N on GaN/sapphire substrates by metalorganic vapor phase epitaxy", Y. Kato, et al., Journal of Crystal Growth 144 (1994) 133-140	
		"The effect of the Si/N treatment of a nitridated sapphire surface on the growth mode of GaN in low-pressure metalorganic vapor phase epitaxy", S. Haffouz, et al., 1998 American Institute of Physics, vol. 73, no. 9, august 31, 1998, p 1278-1280	
		"Influence of in situ sapphire surface preparation and carrier gas on the growth mode of GaN in MOVPE", P. Vennegues, et al., Journal of Crystal Growth, pgs 167-177	
		"Effect of Magnesium and Silicon on the lateral overgrowth of GaN patterned substrates by Metal Organic Vapor Phase Epitaxy", S. Haffouz, et al., MRS Internet Journal Nitride Semiconductor Research, pg 1-6	
		"Growth of high-quality GaN by low-pressure metal-organic vapour phase epitaxy (LP-MOVPE) from 3D islands and lateral overgrowth", H. Lahreche, et al., Journal of Crystal Growth, pgs 245-252	
		"Anti-Surfactant in III-Nitride Epitaxy -Quantum Dot Formation and Dislocation Termination-", S. Tanaka, et al, Appl. Vol. 39 (2000) pp L831-834	
		"Growth Morphology and the Equilibrium Shape: The Role of "Surfactants" in Ge/Si Island Foundation", D. Eaglesham, et al., Physical Review Letters, Vol. 70, No. 7, pgs 996-968	
		"Reduction mechanisms for defect densities in GaN using one-or two-step epitaxial lateral overgrowth methods", P. Vennegues, et al., Journal of Applied Physics, vol. 87, no. 9	
		"The effect of H <sub>2</sub> on morphology evolution during GaN metalorganic chemical vapor deposition", J. Han, et al., Appl. Phys. Lett. 71, 24 Nov. 1997, pgs 3114-3116	
		"Optimization of Si/N Treatment Time of Sapphire Surface and Its Effect on the MOVPE GaN Overlayers", S. Haffouz, et al., pgs 677-681	
		"Oscillator strengths for optical band-to-band processes in GaN epilayers", B. Gil, Physical Review B, vol, 54, No. 11, 1996 The American Physical Society, pgs 7678-7681	
		"High-Resolution Photoluminescence and Reflectance Spectra of Homoepitaxial GaN Layers", K. Kornitzer, et al., pg 5-9	
Lee		"Dynamics of excitonic recombination and interactions in homoepitaxial GaN", K. Korona, 2002 the American Physical Society, 8 pages	

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Considered

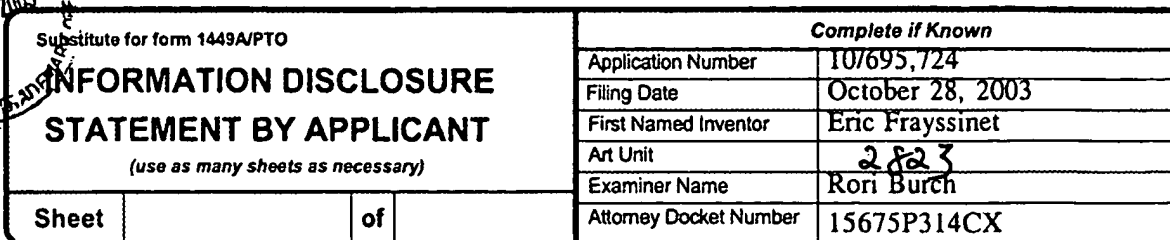
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<sup>1</sup>Applicant's unique citation designation number. <sup>2</sup>Applicant is to place a check mark here if English language Translation is attached.

Based on PTO/SB/088 (08-03) as modified by Blakely, Sokoloff, Taylor & Zafman (wlr) 08/11/2003.  
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